

IN THE CLAIMS:

Please amend the claims as follows:

Claims 1-8 (Canceled)

9. (currently amended) A heat treating method ~~for comprising the steps of distributing defects in a silicon single crystal wafer, said wafer comprising a surface region of several tens of μm deep and an adjacent central region, said wafer having been prepared from a perfect crystal free from grown-in defects and produced by a Czochralski method, said defects being uniformly distributed in a region consisting essentially of the central region a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method,~~ comprising by a first step of maintaining a first heat treatment temperature for an initial entry of the silicon single crystal wafer up to 500°C , and a second step of maintaining a temperature ramping rate in a temperature range from the first heat treatment temperature to a second heat treatment temperature of 700°C - 900°C , said ramping rate being $1^{\circ}\text{C}/\text{min}$ or less, ~~said first step being performed first after a wafer slicing process.~~

10. (currently amended) A heat treating method ~~for comprising the steps of distributing defects in a silicon single crystal wafer, said wafer comprising a surface region of several tens of μm deep and an adjacent central region, said wafer having been prepared from a perfect crystal free from grown-in defects and produced by a Czochralski method, said defects being uniformly distributed in a region consisting essentially of the central region a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method,~~ comprising by a first step of maintaining a first heat treatment temperature for an initial entry of the silicon single crystal wafer up to 500°C , and a second step of maintaining a temperature ramping rate in a temperature range from the first heat treatment temperature to a second heat treatment temperature of 700°C - 900°C , said ramping rate being $1^{\circ}\text{C}/\text{min}$ or less, so as to make uniform the distribution of an oxide precipitate density of the silicon single crystal wafer in the wafer, said first step being performed first after a wafer slicing process.

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